

DUAL FULL BRIDGE

PRODUCT PREVIEW

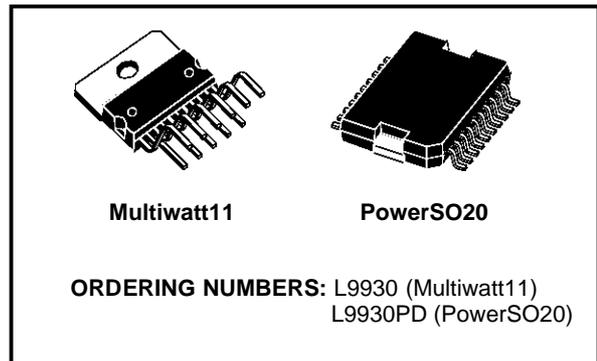
- $R_{DS\ ON} = 2\Omega$
- INTERNAL CLAMPING VOLTAGE = 32V
- INTERNAL FREE WHEELING DIODES
- PARALLEL DRIVE CAPABILITY
- RESISTIVE OR INDUCTIVE LOAD

PROTECTION:

- TEMPERATURE PROTECTION
- SHORT-CIRCUIT PROTECTION (V_{bat} , LOAD, GND)

DETECTION:

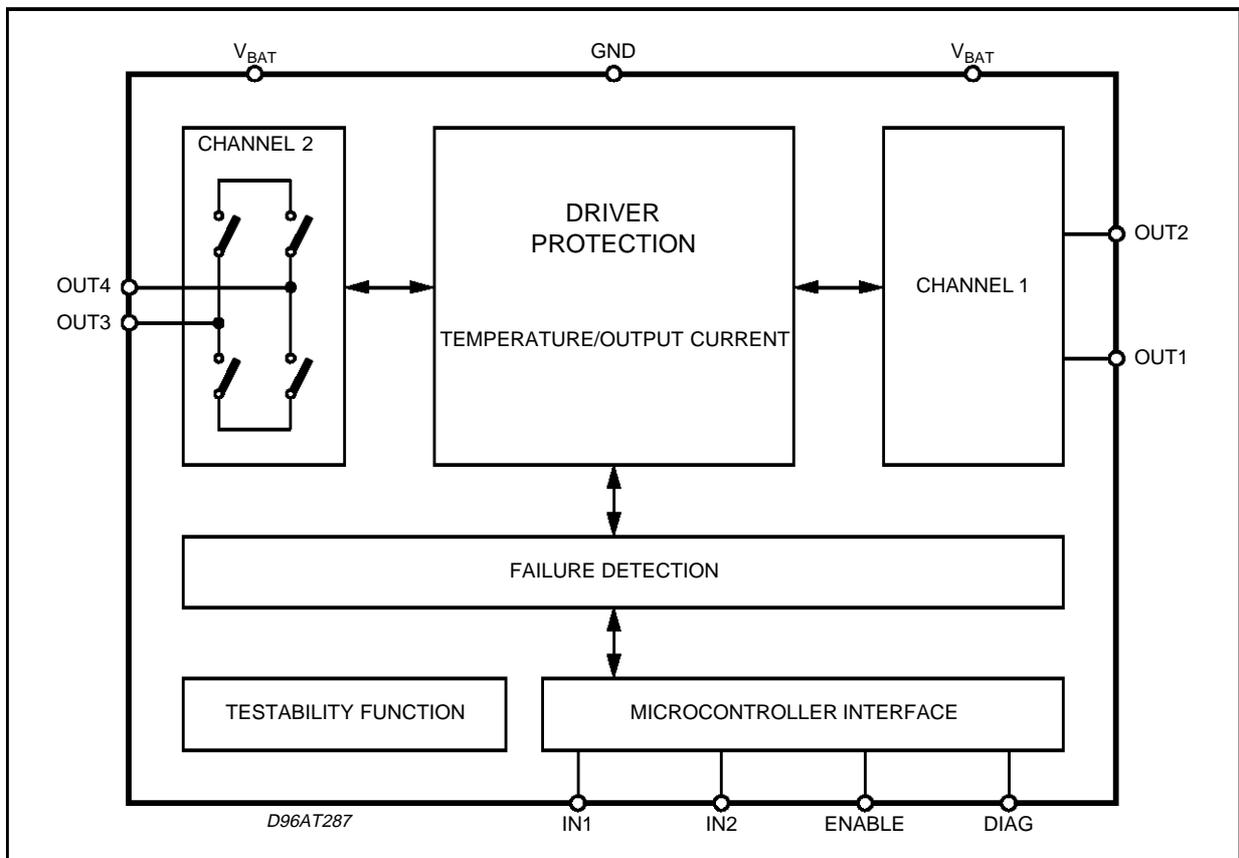
- SHORTED LOAD
- OPEN LOAD



DESCRIPTION

The L9930 is a dual full-bridge. The output stages are Power Mos switches.

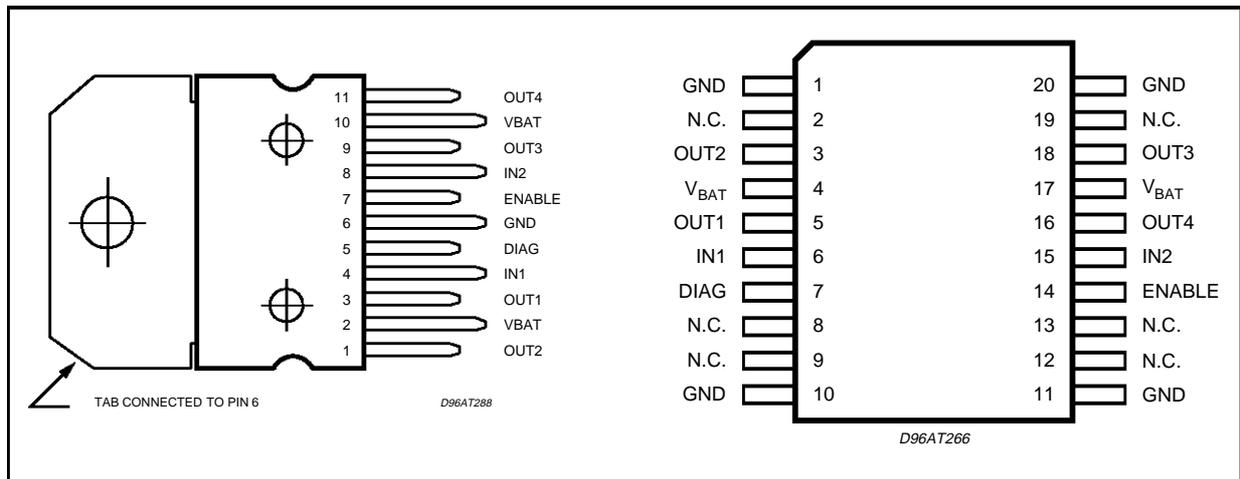
BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
E	Clamped Energy at the Switching off	70	mJ
V _{out DC}	Continuous Output Voltage	24	V
V _{out tr}	Transient Output Voltage	32	V
V _{bat DC}	Continuous Battery Voltage	8 to 24	V
V _{bat tr}	Transient Battery Voltage	45	V
I _{out}	Reverse Output Current	- 2	A
f _{in}	Input Frequency	500	Hz
V _{in}	Input Voltage	- 0.3 to +7	V
V _{diag}	Diagnostic Voltage	- 0.3 to +7	V
T _s	Storage Temperature	- 55 to 150	°C
T _j	Operating Junction Tem	- 40 to 150	°C
V _{ESD}	V _{ESD} (Note MIL STD 883C)	3000	V

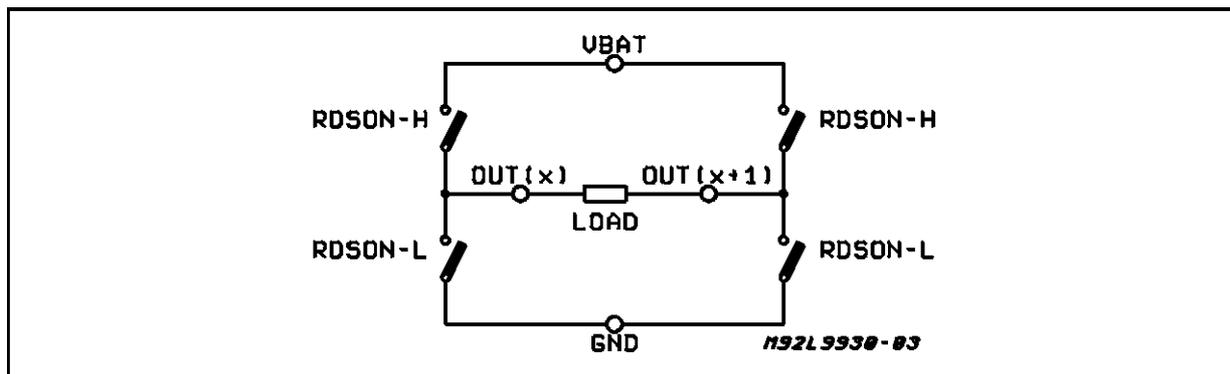
PIN CONNECTION



PIN FUNCTIONS

MW11	PowerSO20	Name	Function
1	3	OUT 2	Output Channel 1
2	4	V _{BAT}	Power Supply
3	5	OUT 1	Output Channel 1
4	6	IN 1	Input Channel 1
5	7	DIAG	Diagnostic Output Common for the 2 Channels
6	1, 10, 11, 20	GND	Ground
7	14	ENABLE	Enable
8	15	IN 2	Input Channel 2
9	18	OUT 3	Output Channel 2
10	17	V _{BAT}	Power Supply
11	16	OUT 4	Output Channel 2
	2, 8, 9, 12, 13, 19	NC	Not Connected

H - BRIDGE CONFIGURATION



THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th\ j-case}$	Thermal Resistance Junction to Case	max.	$^{\circ}C/W$
$R_{th\ j-amb}$	Thermal resistance Junction to Ambient	max.	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($V_{bat} = 8$ to $18V$ $t_J = -40$ to $+150^{\circ}C$, unless otherwise specified.)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_{DSon-H}	ON Resistance	$I_{out} = 0.5A$		2	4.3	Ω
R_{DSon-L}	ON Resistance	$I_{out} = 0.5A$		2	4.3	Ω
V_{OCL}	Clamping Voltage	$I_{out} = 0.1A$		32		V
V_F	Clamp Diode Forward Voltage	$I_{out} = 0.5A$ (see fig. 1)		1.3		V
T_R	Output Voltage Rise Time	$V_{out}; 0.1$ to $0.9 V_{out}$ (see fig. 1)		50	100	μs
T_F	Output Voltage Fall Time	$V_{out}; 0.9$ to $0.1 V_{out}$ (see fig. 1)		50	100	μs
T_{DR}	Input to Output Rising edge Delay	$0.5 V_{IN}$ to $0.1 V_{OUT}$ (see fig. 1)			50	μs
T_{DF}	Input to Output Falling Edge Delay	$0.5 V_{IN}$ to $0.9 V_{OUT}$ (see fig. 1)			50	μs

OUTPUT PROTECTIONS CHARACTERISTICS

I_{SC}	Short Circuit	$T_{amb} = -40^{\circ}C$	0.45		2.4	A
		$T_{amb} = 25^{\circ}C$	0.38		2.4	A
		$T_{amb} = 125^{\circ}C$	0.28		2.4	A
T_{SD}	Temperature		160			$^{\circ}C$
T_{HYST}	Temperature Hysteresis			20		$^{\circ}C$

These protections switch off the full bridge.

OUTPUT DETECTIONS CHARACTERISTICS

R_{OPL-L}	Open-load Threshold Resistor		100			Ω
R_{OPL-H}			200			Ω

SUPPLY CHARACTERISTICS

I_{QHI}	Supply Current	$I_{out1-R} = I_{out2-R} = 0.5A$ $I_{out1-L} = I_{out2-L} = 0.5A$ $V_{BAT} = 14V$			15	mA
I_{QLO}		$R_{load1} = R_{load2} = 50\Omega$ $V_{BAT} = 12V, ENABLE = 0$			0.5	mA

ELECTRICAL CHARACTERISTICS

INPUTS CHARACTERISTICS (normal and standby mode)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V _{IH}	High Threshold				4	V
V _{IL}	Low Threshold		1			V
I _{NHI}	Input Current 1	V _{IN} = 4V			200	μA
I _{NLO}	Input Current 2	V _{IN} = 1V			200	μA

DIAGNOSTIC CHARACTERISTICS

V _{DIAGL}	Low Level Voltage	I _{DIAG} = 2mA		0.6	0.8	V
I _{DIAGH}	Leakage Current	V _{DIAG} = 5.25V		5	10	μA

INITIALIZATION CHARACTERISTICS

T _{INIT}	Initialization Timing	V _{BAT} = 12V	10			μs
T _{STUP}	Start-Up Timing	V _{BAT} = 12V	1			ms

TRUE TABLE

ENAB	IN1	IN2	OUT1	OUT2	OUT3	OUT4	MODE	DIAG
0	0	0	HZ	HZ	HZ	HZ	STANDBY	?
0	0	1	HZ	HZ	HZ	HZ	NORMAL	?
0	1	0	HZ	HZ	HZ	HZ	NORMAL	?
0	1	1	HZ	HZ	HZ	HZ	NORMAL	?
1	0	0	HSD	LSD	HSD	LSD	NORMAL	VALID
1	0	1	HSD	LSD	LSD	HSD	NORMAL	VALID
1	1	0	LSD	HSD	HSD	LSD	NORMAL	VALID
1	1	1	LSD	HSD	LSD	HSD	NORMAL	VALID

Figure 1: Initialization.

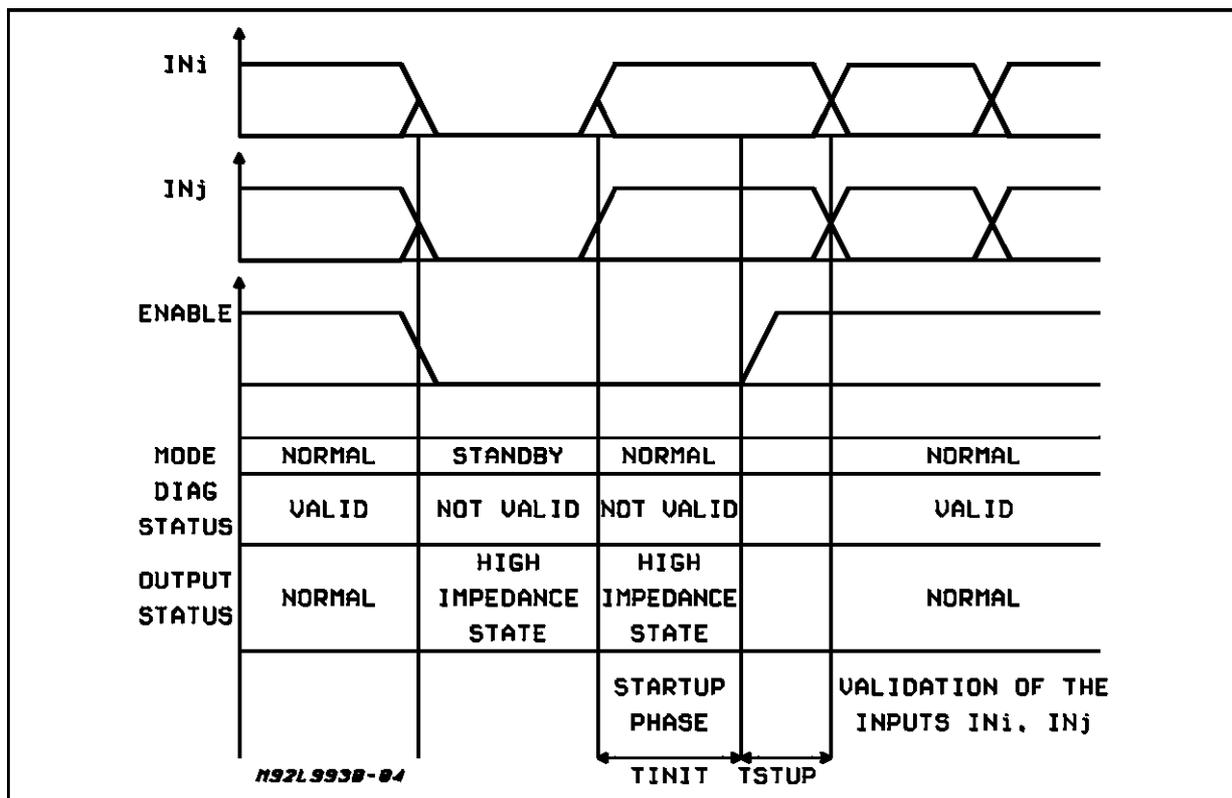


Figure 2: Normal Condition.

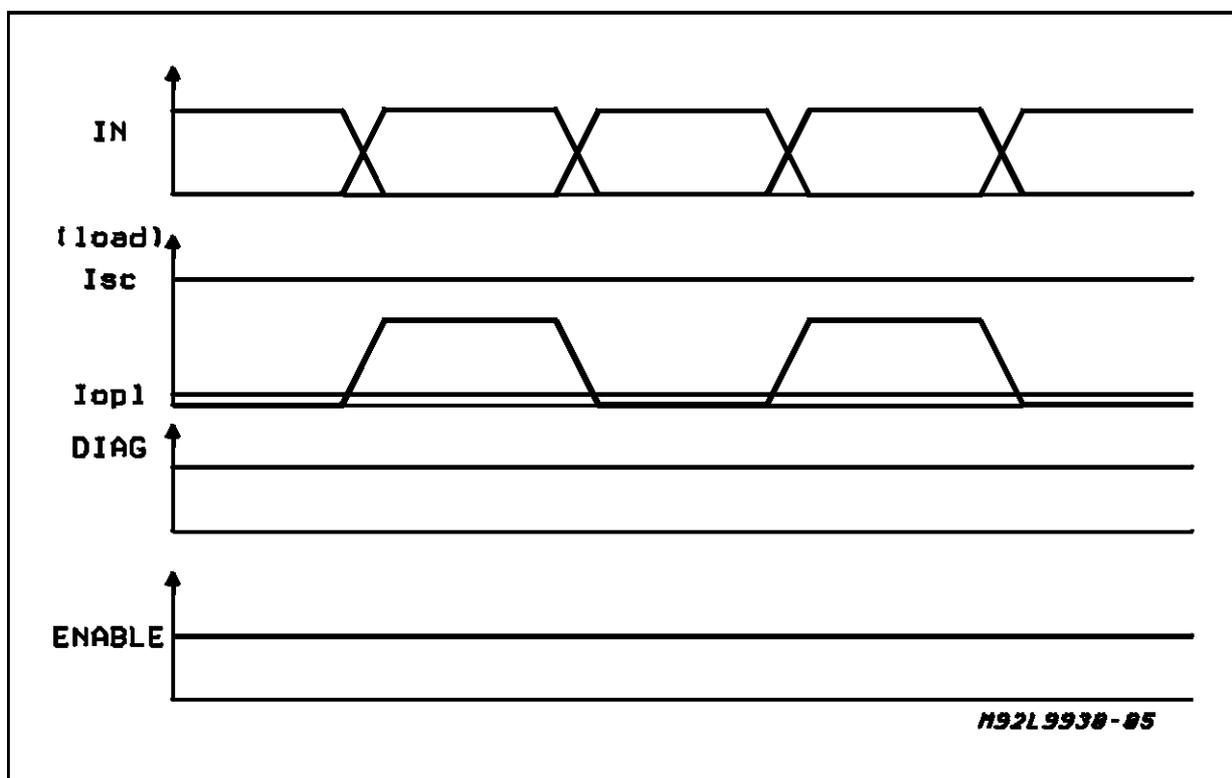


Figure 3: Short-circuit Condition.

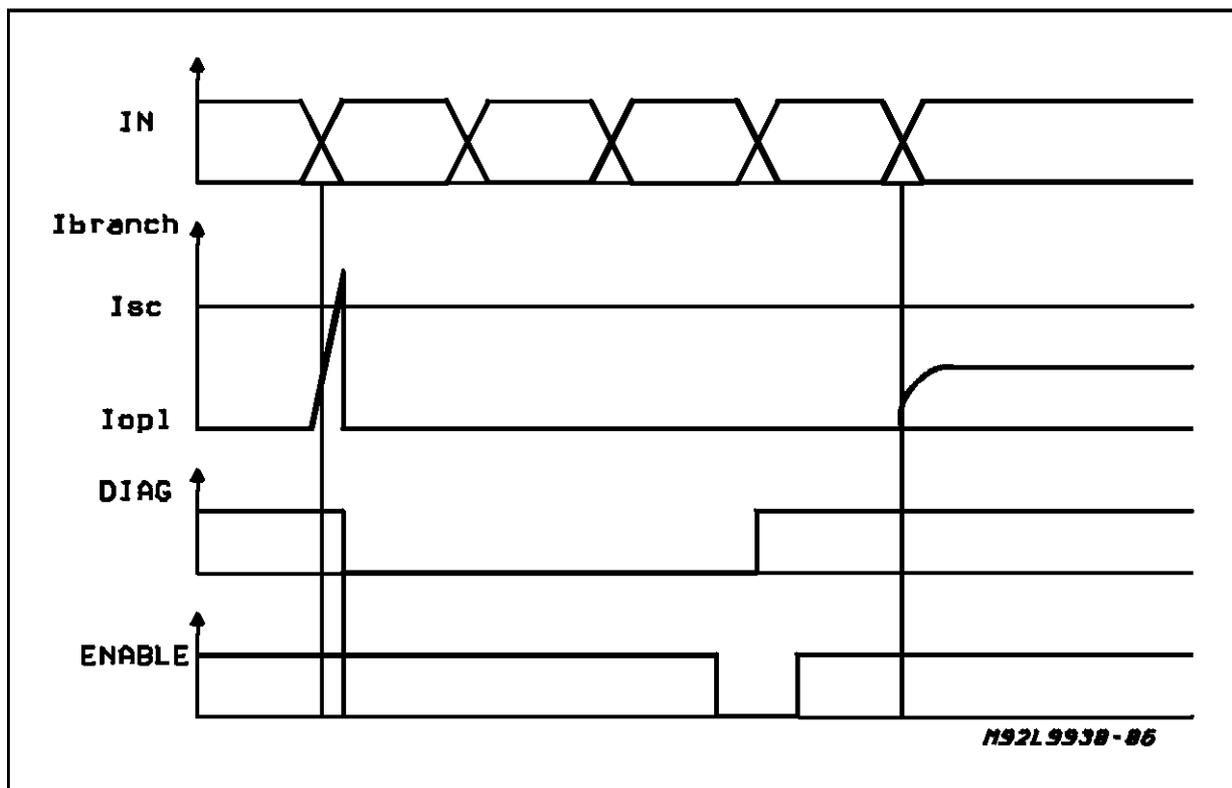
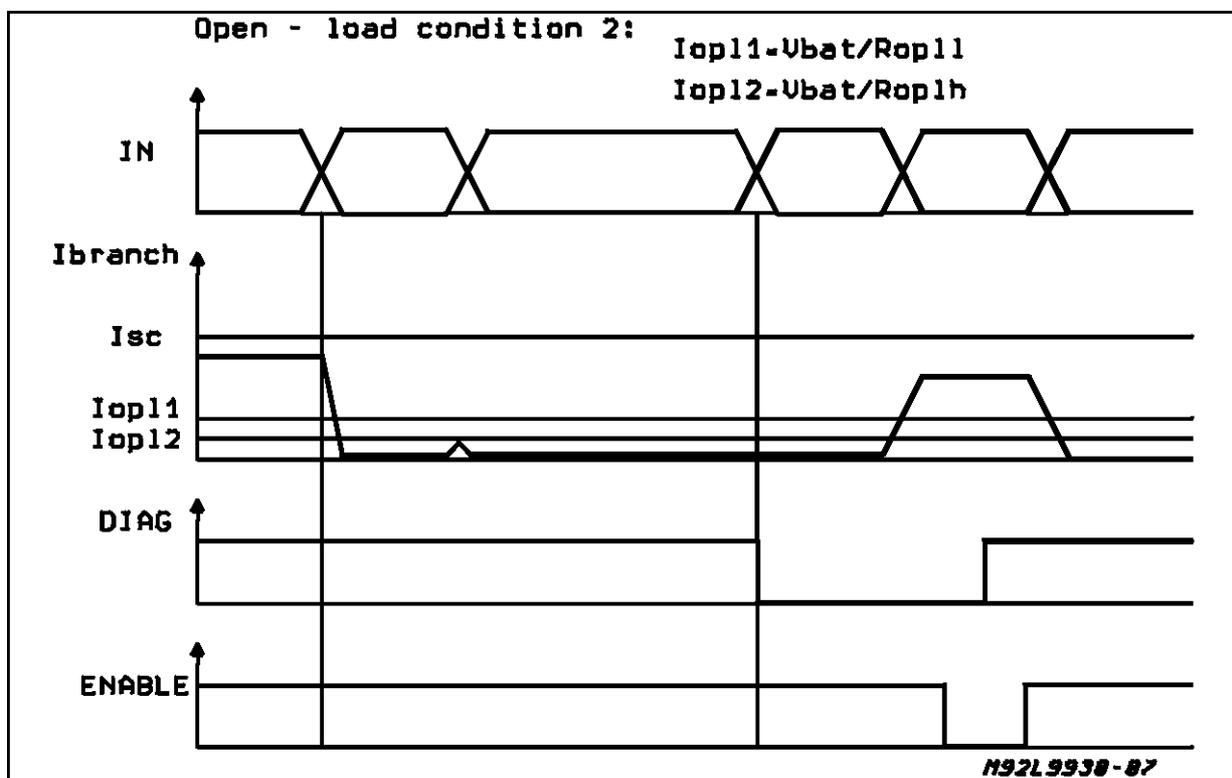
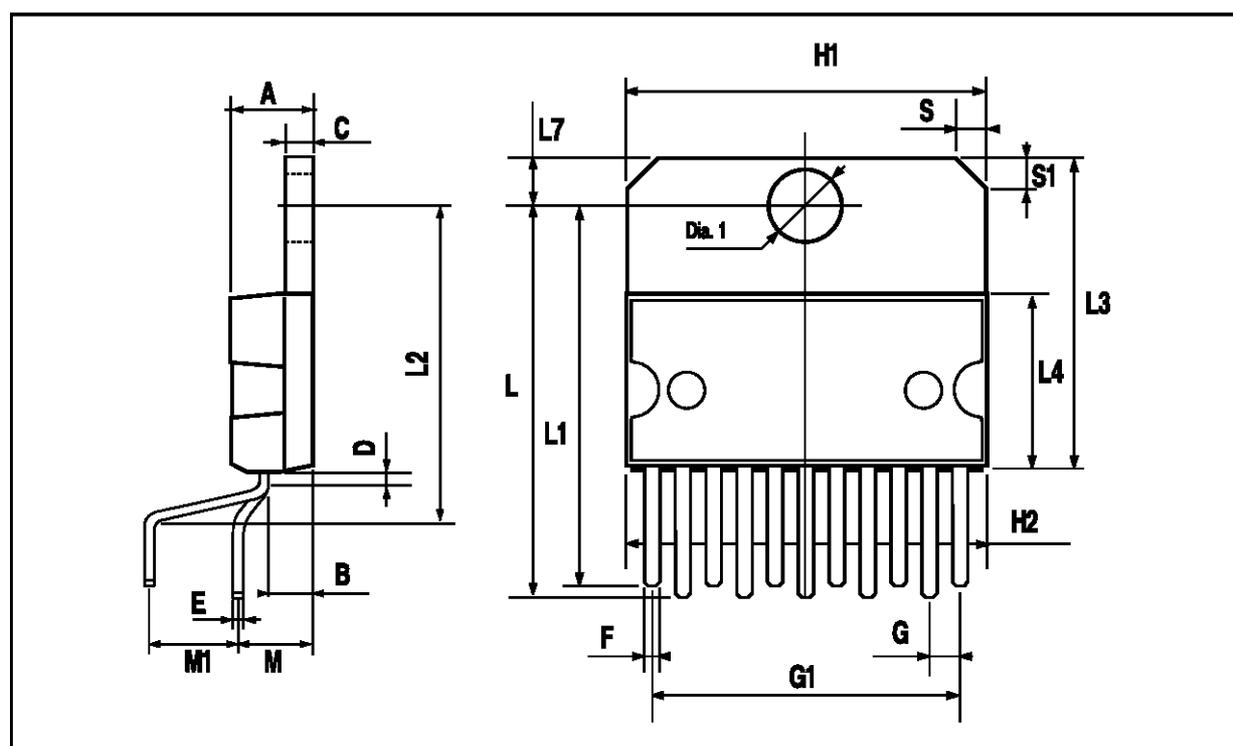


Figure 4.



MULTIWATT11 PACKAGE MECHANICAL DATA

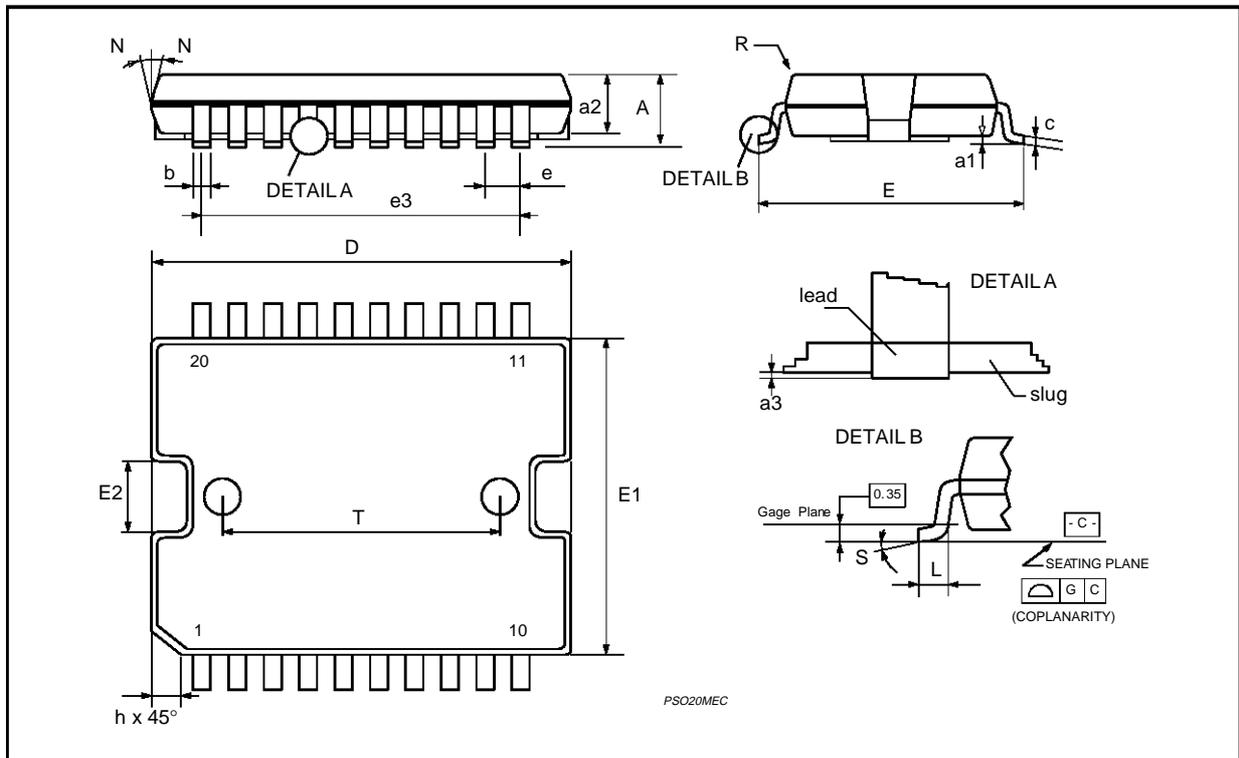
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			5			0.197
B			2.65			0.104
C			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.88		0.95	0.035		0.037
G	1.45	1.7	1.95	0.057	0.067	0.077
G1	16.75	17	17.25	0.659	0.669	0.679
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.87	0.886
L2	17.4		18.1	0.685		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
M	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.73	5.08	5.43	0.186	0.200	0.214
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152



PowerSO20 PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			3.60			0.1417
a1	0.10		0.30	0.0039		0.0118
a2			3.30			0.1299
a3	0		0.10	0		0.0039
b	0.40		0.53	0.0157		0.0209
c	0.23		0.32	0.009		0.0126
D (1)	15.80		16.00	0.6220		0.6299
E	13.90		14.50	0.5472		0.570
e		1.27			0.050	
e3		11.43			0.450	
E1 (1)	10.90		11.10	0.4291		0.437
E2			2.90			0.1141
G	0		0.10	0		0.0039
h			1.10			
L	0.80		1.10	0.0314		0.0433
N	10° (max.)					
S	8° (max.)					
T		10.0			0.3937	

(1) "D and E1" do not include mold flash or protrusions
 - Mold flash or protrusions shall not exceed 0.15mm (0.006")



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